

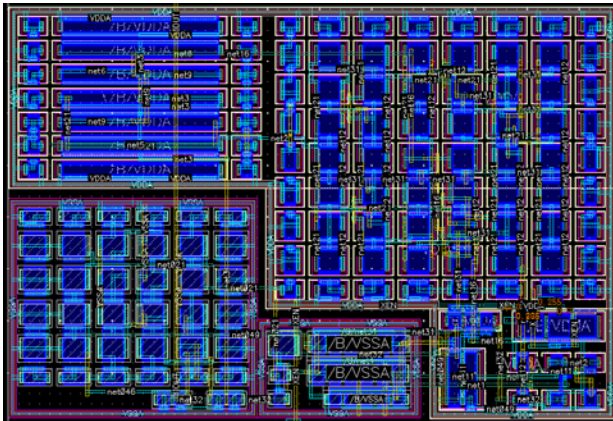
IBIAS8

Ultra-Low-Power Proportional to Absolute Temperature (I_{PTAT}) Bias Current Source. Proof of silicon with typical/preliminary measurements available. (Please contact sales@ailinear.com)

Parameter	Typical Spec	Condition
I_{DD} (nA)	11	$V_{DD}=2v$, Temperature = 27C
V_{DD} Low (v)	0.9	V_{DD} sweep $0v \rightarrow 2.2v$, Temperature = 27C
V_{DD} High (v)	2	V_{DD} sweep $0v \rightarrow 2.2v$, Temperature = 27C
TC (%/C)	0.5	$V_{DD}=2v$, $\Delta T \sim 30C$
VC (%/V)	0.3	V_{DD} sweep $1v \rightarrow 2.2v$, Temperature = 27C

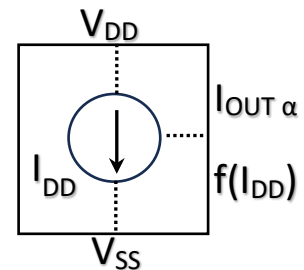
** see disclaimer

Cell Layout



Cell Size $\sim 60\mu m \times 40\mu m$ in TSMC 180nm CMOS

Block Diagram



Features:

- Programmable (pre or post silicon) I_{OUT} that tracks I_{DD}
- Tiny CMOS ($\sim 60\mu m \times 40\mu m$) bias current Intellectual Property (IP) cell operating in subthreshold with ultra-low current consumption I_{DD} (typical 11nA)
- Large value but tiny active bias resistor (R_{PMOS}) as a function of PMOSFET keeps I_{DD} ultra-low
- Most suitable for SoC whose analog (e.g., oscillator, comparator, ADC) performance best correlates with PMOSFET parameters
- Utilized regulated cascode current mirrors (RGC) to enhance I_{BIAS} voltage V_{DD} coefficient
- Suitable for SoC where I_{BIAS} is more optimized when PTAT Kirkoff Voltage Loop (KVL) is coupled to V_{DD}
- I_{DD} and I_{OUT} absolute value mostly a function of PMOSFET mobility (μ) inherently more stable to help narrow I_{DD} variation over fabrication process corners
- Based on 180nm digital CMOS at TSMC and portable to smaller fabrication nodes.